

1    ABSTRACT OF THE DISCLOSURE

          A semiconductor device comprises at least a  
semiconductor layer including source and drain areas  
of a first conductive type and of a high impurity  
5    concentration and a channel area positioned between  
the source and drain areas, an insulation layer  
covering at least the channel area, and a gate  
electrode positioned close to the insulation layer.  
The channel area at least comprises a first channel  
10    area of a low resistance, positioned close to the  
insulation layer and having a second conductive type  
opposite to the first conductive type, and a second  
channel area of a high resistance, having the first  
conductive type and positioned adjacent to the first  
15    channel area.

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